

SPTECH Silicon PNP Power Transistor**2SA1232****DESCRIPTION**

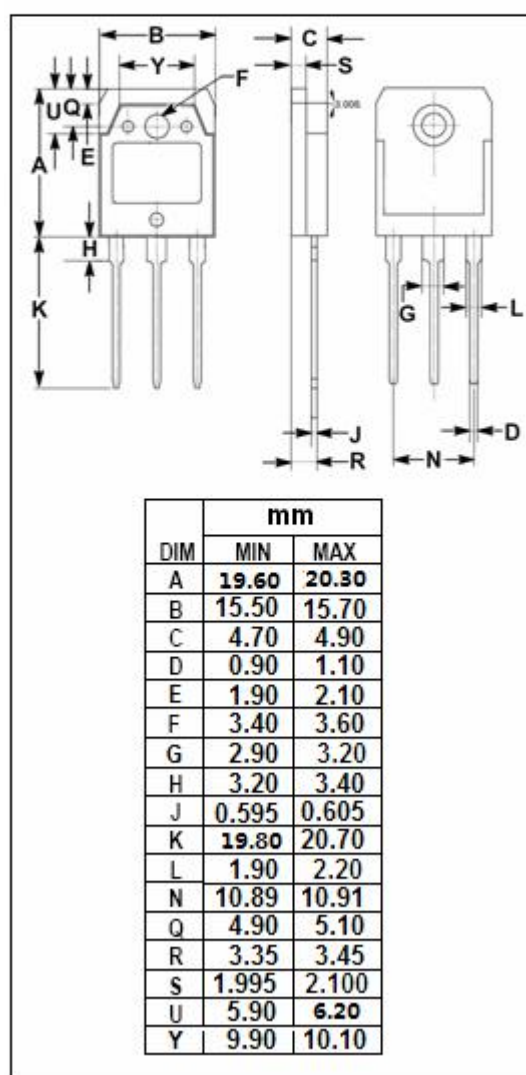
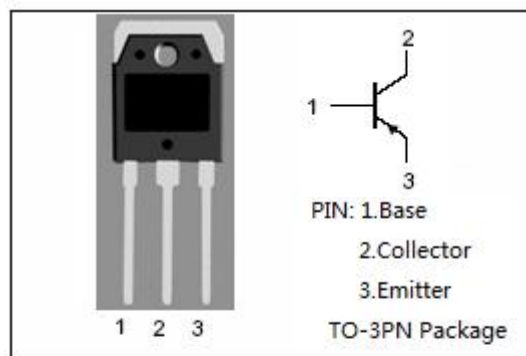
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -130V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC3012

APPLICATIONS

- For audio frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-130	V
V_{CEO}	Collector-Emitter Voltage	-130	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	100	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon PNP Power Transistor**2SA1232****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -5.0A; I _B = -0.5A			-1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -5.0A; I _B = -0.5A			-2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -130V; I _E = 0			-50	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -3V; I _C = 0			-50	μ A
h _{FE-1}	DC Current Gain	I _C = -2A; V _{CE} = -5V	60		320	
h _{FE-2}	DC Current Gain	I _C = -5A; V _{CE} = -5V	40			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1.0MHz		250		pF
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -5V		60		MHz

◆ **h_{FE-1} Classifications**

R	Q	P
60-120	100-200	160-320